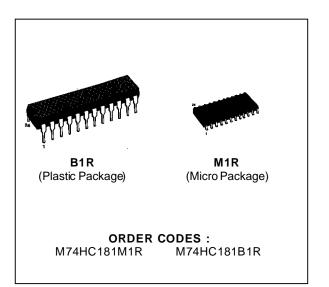


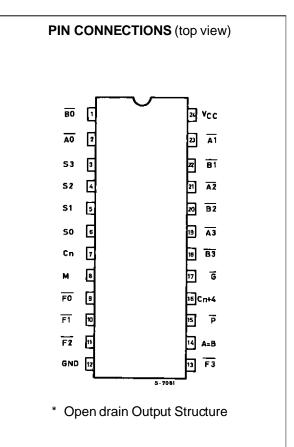
## ARITHMETIC LOGIC UNIT/FUNCTION GENERATOR

- HIGH SPEED t<sub>PD</sub> = 13 ns (TYP.) AT V<sub>CC</sub> = 5 V
- LOW POWER DISSIPATION
- I<sub>CC</sub> = 4 μA (MAX.) at T<sub>A</sub> = 25 °C HIGH NOISE IMMUNITY
- V<sub>NIH</sub> = V<sub>NIL</sub> = 28 % V<sub>CC</sub> (MIN.) ■ OUTPUT DRIVE CAPABILITY
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE |I<sub>OH</sub>| = I<sub>OL</sub> = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tPLH = tPHL
- WIDE OPERATING VOLTAGE RANGE V<sub>CC</sub> (OPR) = 2 V to 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS181

#### DESCRIPTION

The 74HC181 is a high speed CMOS ARITHMETIC LOGIC UNIT/FUNCTION GENERATOR fabricated with silicon gate  $C^2MOS$  technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. These circuits perform 16 binary arithmetic operations on two 4-bit words as shown in tables 1 and 2. These operations are selected by the four function-select lines (S0, S1, S2, S3) and include addition, subtraction, decrement, and straight transfer. When performing arithmetic manipulations, the internal carries must be enabled by applying a low-level voltage to the mode control input (M). A full carry look-ahead scheme is made available in these devices for fast, simultaneous carry generation by means of two cascade-outputs (pins 15 and 17) for the four bits in the package. When used in coniunction with the M54HC182 or M74HC182, full carry look-ahead circuits, high-speed arithmetic operations can be performed. These circuits will accomodate active-high or active-low data, if the pin designations are interpreted as shown below. Subtraction is accomplished by 1,s complement addition where the 1's complement of the subtrahend is generated internally. The resultant output is 1-B-1, which requires an endaround or forced carry to produce A-B. The 181 can also be utilized as a comparator. The A = B output is internally decoded from the function outputs (F0, F1, F2, F3) so that when two words of equal magnitude are applied at the A and B inputs, it will assume a high level to indicated equality (A = B). The ALU should be

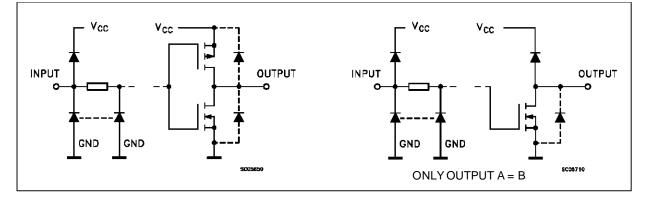




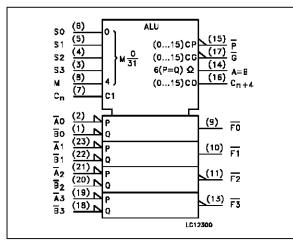
#### **DESCRIPTION** (continued)

in the subtract mode with  $C_n = H$  when performing this comparison. The A = B output is open-drain so that it can be wire-AND connected to give a comparison for more that four bits. The carry output (Cn + 4) can also be used to supply relative magnitude information. Again, the ALU should be placed in the subtract mode by placing the function select inputs S3, S2, S1, S0 at L, H, H, L, respectively. These circuits have been designed to not only incorporate all of the designer's requirements for arithmetic operations, but also to provide 16 possible functions of two Boolean variables without the use of external circuitry. These logic functions are selected by use of the four function-select inputs (S0, S1, S2, S3) with the mode-control input (M) at a high level to disable the internal carry. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

#### INPUT AND OUTPUT EQUIVALENT CIRCUITS



#### IEC LOGIC SYMBOLS



#### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
2, 23, 21, 19	$\overline{A0}$ to $\overline{A3}$	Word A Inputs
1, 22, 20, 18	$\overline{B0}$ to $\overline{B3}$	Word B Inputs
6, 5, 4, 3	S0 to S3	Function Select Inputs
7	Cn	Inv. Carry Input
8	М	Mode Control Input
9, 10, 11, 13	$\overline{F0}$ to $\overline{F3}$	Function Outputs
14	A = B	Comparator Output
15	IΡ	Carry Propagate Output
16	Cn + 4	Inv. Carry Output
17	IJ	Carry Generate Output
12	GND	Ground (0V)
24	V <sub>CC</sub>	Positive Supply Voltage

PIN NUMBER	2	1	23	22	21	20	19	18	9	10	11	13	7	16	15	17
ACTIVE LOW DATA (Table 1)	A0	B0	A1	B1	A2	B2	A3	B3	F0	F1	F2	F3	Cn	Cn + 4	P	0
ACTIVE HIGH DATA (Table 1)	A0	B0	A1	B1	A2	B2	A3	B3	F0	F1	F2	F3	Cn	Cn + 4	Х	Y

Input Cn	Output Cn + 4	Active LOW Data (Figure 1)	Active HIGH Data (Figure 2)
Н	Н	$A \ge B$	$A \leq B$
Н	L	A < B	A > B
L	Н	A > B	A < B
L	L	A ≤ B	$A \ge B$

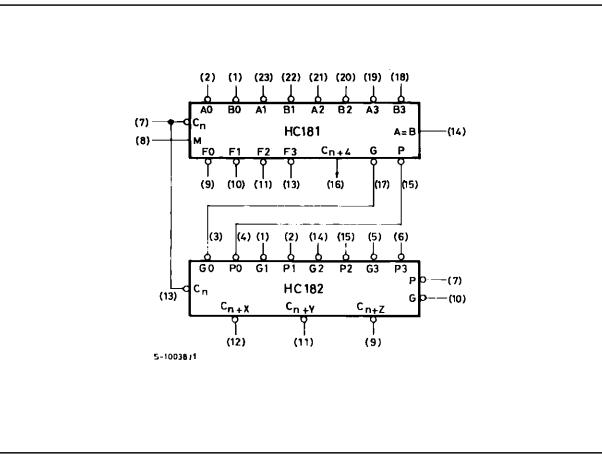


	Solo	ction			ACTIVE LOW DA	ТА
	Sele	Clion		M = H Logic	M = L: Arithn	netic Operations
S3	S2	S1	S0	Functions	Cn = L (no carry)	Cn = H (with carry)
L	L	L	L	$F = \overline{A}$	F = A Minus 1	F = A
L	L	L	н	$F = \overline{AB}$	F = AB Minus 1	F = AB
L	L	Н	L	$F = \overline{A} + B$	$F = A\overline{B}$ Minus 1	$F = (A\overline{B})$
L	L	Н	н	F = 1	F = Minus 1 (2's Compl)	F = Zero
L	Н	L	L	$F = \overline{A + B}$	$F = A Plus (A + \overline{B})$	$F = A Plus (A + \overline{B}) Plus 1$
L	Н	L	Н	$F = \overline{B}$	F = AB Plus (A + B)	$F = AB Plus (A + \overline{B}) Plus 1$
L	Н	Н	L	$F = \overline{A \oplus B}$	F = A Minus B Minus 1	F = A Minus B
L	н	н	н	$F = A + \overline{B}$	$F = A + \overline{B}$	$F = (A + \overline{B}) Plus 1$
Н	L	L	L	$F = \overline{A}B$	F = A Plus (A + B)	F = A Plus (A + B) Plus 1
Н	L	L	н	F = A ⊕ B	F = A Plus B	F = A Plus B Plus 1
Н	L	Н	L	F = B	$F = A\overline{B} Plus (A + B)$	$F = A\overline{B}$ Plus (A + B) Plus 1
Н	L	Н	н	F = A + B	F = A + B	F = (A + B) Plus 1
Н	Н	L	L	F = 0	F = A Plus A *	F = A Plus A Plus 1
Н	Н	L	н	$F = A\overline{B}$	F = AB Plus A	F = AB Plus A Plus 1
Н	н	Н	L	F = AB	$F = A\overline{B}$ Plus A	$F = A\overline{B}$ Plus A Plus 1
Н	н	н	н	F = A	F = A	F = A Plus 1

#### TRUTH TABLE 1

\* Each bit is shifted to the next more significant position.

#### **FIGURE 1**



SGS-THOMSON

NICROELECTRONICS

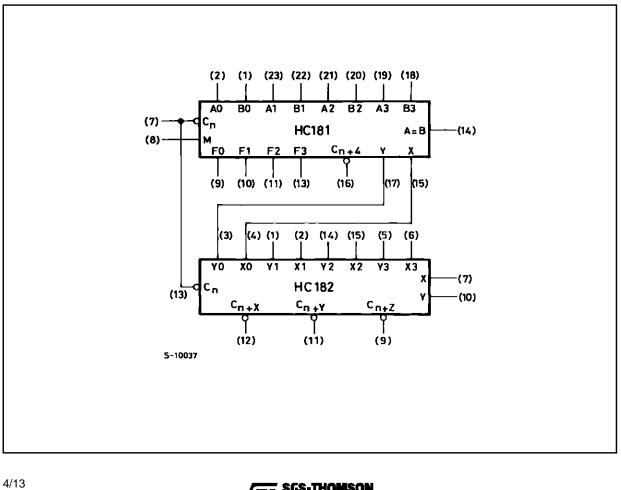
5/

#### **TRUTH TABLE 2**

	Solo	ction			ACTIVE HIGH DAT	ГА
	Sele	CHOIL		M = H Logic	M = L: Arithm	etic Operations
S3	S2	S1	S0	Functions	Cn = H (no carry)	Cn = L (with carry)
L	L	L	L	$F = \overline{A}$	F = A	F = A Plus 1
L	L	L	н	$F = \overline{A + B}$	F = A + B	F = (A + B) Plus 1
L	L	Н	L	$F = \overline{A}B$	$F = A + \overline{B}$	$F = (A + \overline{B})$ Plus 1
L	L	Н	Н	F = 0	F = Minus 1 (2's Compl)	F = Zero
L	н	L	L	$F = \overline{AB}$	$F = A Plus (A\overline{B})$	$F = A Plus A\overline{B} Plus 1$
L	н	L	н	$F = \overline{B}$	F = (A + B) Plus AB	$F = (A + B) Plus (A\overline{B}) Plus 1$
L	н	Н	L	$F = A \oplus B$	F = A Minus B Minus 1	F = A Minus B
L	н	н	н	$F = A\overline{B}$	$F = A\overline{B}$ Minus 1	$F = A\overline{B}$
Н	L	L	L	$F = \overline{A} + B$	F = A Plus AB	F = A Plus AB Plus 1
Н	L	L	н	$F = \overline{A \oplus B}$	F = A Plus B	F = A Plus B Plus 1
Н	L	Н	L	F = B	$F = (A + \overline{B})$ Plus AB	$F = (A + \overline{B})$ Plus AB Plus 1
Н	L	Н	Н	F = AB	F = AB Minus 1	F = AB
Н	н	L	L	F = 1	F = A Plus A *	F = A Plus A Plus 1
Н	н	L	Н	$F = A + \overline{B}$	F = (A + B) Plus A	F = (A + B) Plus A Plus 1
Н	н	Н	L	F = A + B	$F = (A + \overline{B})$ Plus A	$F = (A + \overline{B})$ Plus A Plus 1
Н	Н	Н	Н	F = A	F = A Minus 1	F = A

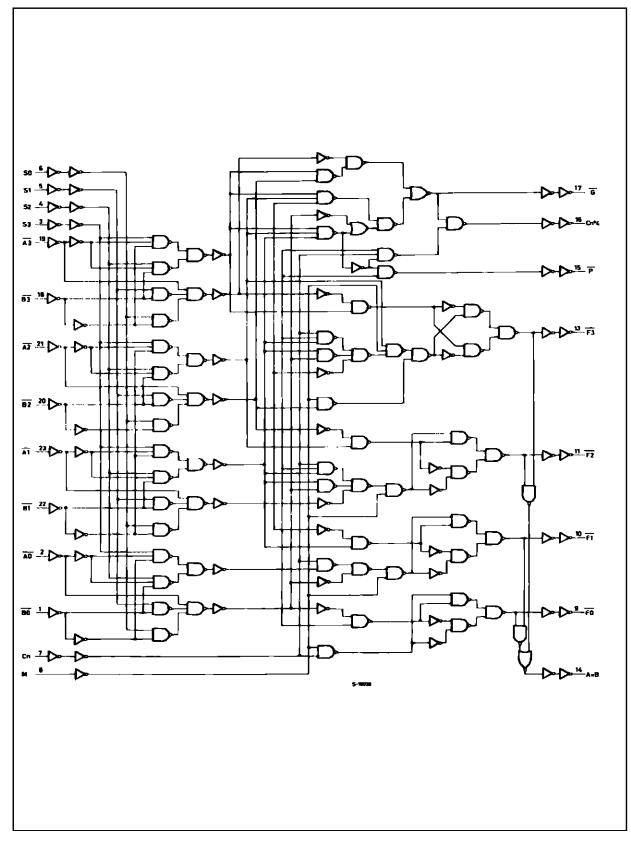
\* Each bit is shifted to the next more significant position.

#### **FIGURE 2**





#### LOGIC DIAGRAM





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
lo	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
PD	Power Dissipation	500 (*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (\*) 500 mW:  $\cong$  65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	Supply Voltage		2 to 6	V
VI	Input Voltage	0 to V <sub>CC</sub>	V	
Vo	Output Voltage	0 to V <sub>CC</sub>	V	
T <sub>op</sub>	Operating Temperature		-40 to +85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	$V_{CC} = 2 V$	0 to 1000	ns
		$V_{CC} = 4.5 V$	0 to 500	
		$V_{CC} = 6 V$	0 to 400	



#### DC SPECIFICATIONS

		Те	est Co	nditions			Value			
Symbol	Parameter	Vcc			T,	<sub>A</sub> = 25 <sup>o</sup>	°C	-40 to	85 °C	Unit
		(V)			Min.	Тур.	Max.	Min.	Max.	
VIH	High Level Input Voltage	2.0			1.5			1.5		
		4.5			3.15			3.15		V
		6.0			4.2			4.2		
V <sub>IL</sub> Lo	Low Level Input	2.0					0.5		0.5	
	Voltage	4.5					1.35		1.35	V
		6.0					1.8		1.8	
Vон Н	High Level Output Voltage	2.0	V.		1.9	2.0		1.9		
	(except A = B output)	4.5	Vi = ViH	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		
		6.0	or		5.9	6.0		5.9		V
		4.5	VIL	I <sub>O</sub> =-4.0 mA	4.18	4.31		4.13		
		6.0		I <sub>0</sub> =-5.2 mA	5.68	5.8		5.63		
V <sub>OL</sub>	Low Level Output Voltage	2.0	VI =			0.0	0.1		0.1	
		4.5	VI =	I <sub>O</sub> = 20 μA		0.0	0.1		0.1	.,
		6.0	or			0.0	0.1		0.1	V
		4.5	Vı∟	I <sub>O</sub> = 4.0 mA		0.17	0.26		0.33	
		6.0		l <sub>0</sub> = 5.2 mA		0.18	0.26		0.33	
h	Input Leakage Current	6.0	V1 = '	V <sub>CC</sub> or GND			±0.1		±1	μA
Icc	Quiescent Supply Current	6.0	VI = '	V <sub>CC</sub> or GND			4		40	μA



#### **AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

		Tes	st Conditions			Value			
Symbol	Parameter	Vcc			$A = 25^{\circ}$ C and 7			85 °C HC	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	
tтLн	Output Transition Time	2.0			30	75		95	
$t_{THL}$		4.5			8	15		19	ns
		6.0			7	13		16	
t <sub>PLH</sub>	Propagation Delay Time	2.0			54	120		150	
t <sub>PHL</sub>	(1)	4.5			16	24		30	ns
		6.0			13	20		26	
t <sub>PLH</sub>	Propagation Delay Time	2.0			90	215		270	
tPHL	(2)	4.5			26	43		54	ns
		6.0			20	37		46	
t <sub>PLH</sub>	Propagation Delay Time	2.0			97	215		270	
tPHL	(3)	4.5			27	43		54	ns
		6.0			21	37		46	
t <sub>PLH</sub>	Propagation Delay Time	2.0			80	180		225	
<b>t</b> PHL	(4)	4.5			23	36		45	ns
		6.0			18	31		38	
tPLH	Propagation Delay Time	2.0			81	190		240	
tPHL	(5)	4.5			24	38		48	ns
		6.0			19	32		41	
t <sub>PLH</sub>	Propagation Delay Time	2.0			80	180		225	
tPHL	(6)	4.5			23	36		45	ns
		6.0			18	31		38	
tPLH	Propagation Delay Time	2.0			80	170		215	
tPHL	(7)	4.5			23	34		43	ns
		6.0			18	29		37	
<b>t</b> PLH	Propagation Delay Time	2.0			80	170		215	
tPHL	(8)	4.5			23	34		43	ns
		6.0			18	29		37	
<b>t</b> PLH	Propagation Delay Time	2.0			95	220		275	
tPHL	(9)	4.5			27	44		55	ns
		6.0			21	37		47	
<b>t</b> PLH	Propagation Delay Time	2.0			95	220		275	
<b>t</b> PHL	(10)	4.5			27	44		55	ns
		6.0			21	37		47	
<b>t</b> PLH	Propagation Delay Time	2.0			86	200		250	
t <sub>PHL</sub>	(11)	4.5			24	40		50	ns
		6.0			18	34		43	
t <sub>PLZ</sub>	Propagation Delay Time	2.0			92	210		265	
t <sub>PZL</sub>	(12)	4.5	$R_L = 1k\Omega$		27	42		53	ns
		6.0			27	36		45	
CIN	Input Capacitance				5	10		10	pF
C <sub>PD</sub> (*)	Power Dissipation Capacitance	+ +			195				pF
C <sub>PD</sub> (*)	Power Dissipation Capacitance				195				

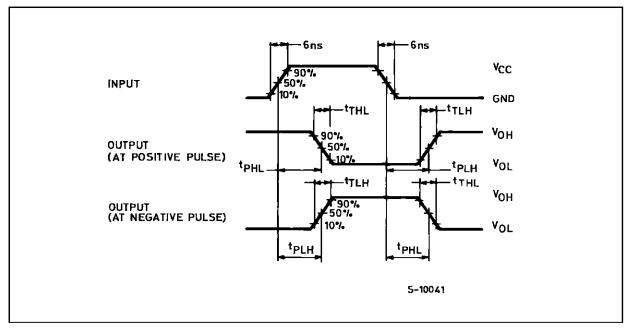
(\*)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation.  $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$ 



Test No	INPUT	OUTPUT	Test Conditions
(1)	Cn	Cn + 4	
(2)	Any $\overline{A}$ or $\overline{B}$	Cn + 4	M = GND, S0 = S3 = $V_{CC}$ , S1 = S2 GND (SUM mode)
(3)	Any $\overline{A}$ or $\overline{B}$	Cn + 4	$M = GND, S0 = S3 = GND, S1 = S2 V_{CC} (DIFF mode)$
(4)	Cn	Any F	$M = GND (\overline{SUM} \text{ or } \overline{DIFF} \text{ mode})$
(5)	Any $\overline{A}$ or $\overline{B}$	G	$M = GND, S0 = S3 = V_{CC}, S1 = S2 GND (\overline{SUM} mode)$
(6)	Any $\overline{A}$ or $\overline{B}$	G	$M = GND$ , $S0 = S3 = GND$ , $S1 = S2 V_{CC}$ (DIFF mode)
(7)	Any $\overline{A}$ or $\overline{B}$	F	$M = GND$ , $S0 = S3 = V_{CC}$ , $S1 = S2 GND$ (SUM mode)
(8)	Any A or B	ΓF	$M = GND$ , $S0 = S3 = GND$ , $S1 = S2 V_{CC}$ (DIFF mode)
(9)	Ai or Bi	Fi	$M = GND$ , $S0 = S3 = V_{CC}$ , $S1 = S2 GND$ (SUM mode)
(10)	Ai or Bi	İFİ	M = GND, S0 = S3 = GND, S1 = S2 $V_{CC}$ (DIFF mode)
(11)	Ai or Bi	Fi	M = V <sub>CC</sub> (Logic mode)
(12)	Any $\overline{A}$ or $\overline{B}$	A = B	$M = GND, S0 = S3 = GND, S1 = S2 V_{CC} (\overline{DIFF} mode)$

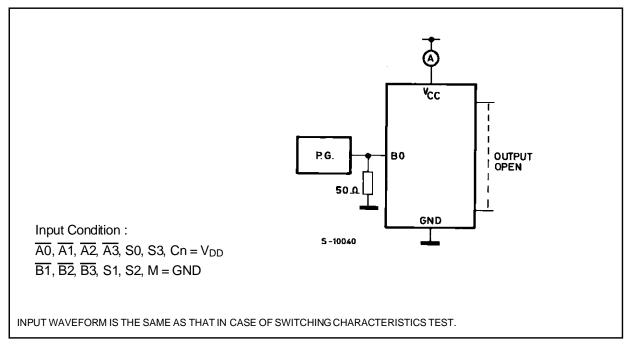
#### **PROPAGATION DELAY TIME TEST CONDITIONS**

#### SWITCHING CHARACTERISTICS TEST WAVEFORM





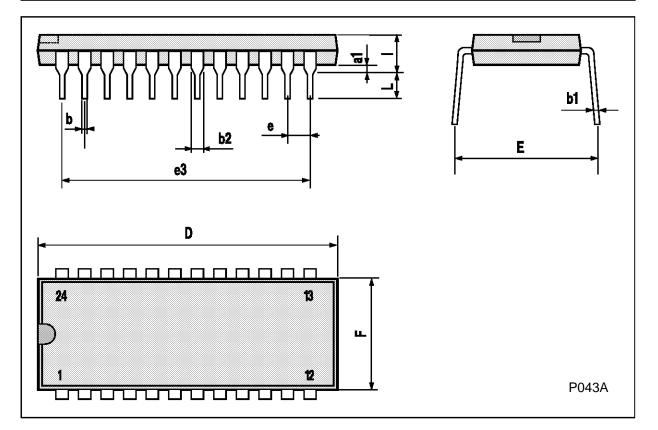
#### TEST CIRCUIT Icc (Opr.)





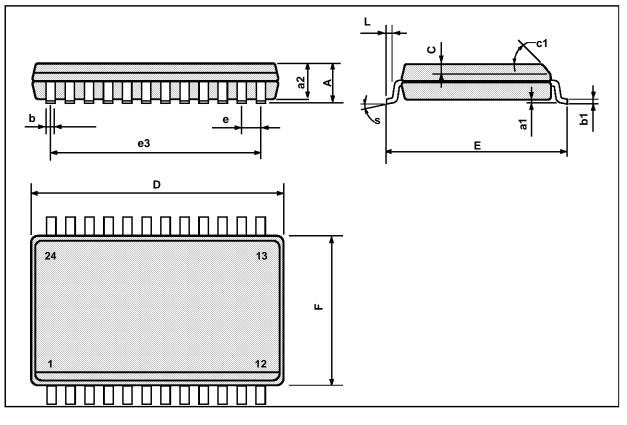
DIM.		mm			inch	
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1		0.63			0.025	
b		0.45			0.018	
b1	0.23		0.31	0.009		0.012
b2		1.27			0.050	
D			32.2			1.268
E	15.2		16.68	0.598		0.657
е		2.54			0.100	
e3		27.94			1.100	
F			14.1			0.555
I		4.445			0.175	
L		3.3			0.130	

## Plastic DIP24 (0.25) MECHANICAL DATA



### SO24 MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
С		0.50			0.020	
c1			45°	(typ.)		
D	15.20		15.60	0.598		0.614
E	10.00		10.65	0.393		0.420
е		1.27			0.05	
e3		13.97			0.55	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
S			8° (r	max.)		



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